

Silicon NPN Power Transistors

2SD1296

DESCRIPTION

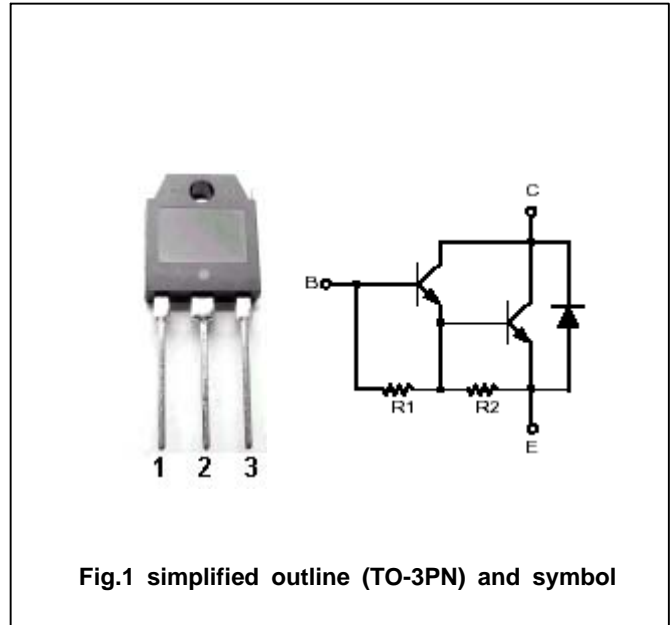
- With TO-3PN package
- High DC current gain
- Low saturation voltage

APPLICATIONS

- For audio frequency power amplifier and low speed high current switching industrial use

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter



Absolute maximum ratings (Ta=25 )

SYMBOL	PARAMETER	CONDITIONS	MAX	UNIT
$V_{CBO}$	Collector-base voltage	Open emitter	150	V
$V_{CEO}$	Collector-emitter voltage	Open base	100	V
$V_{EBO}$	Emitter-base voltage	Open collector	8	V
$I_C$	Collector current		15	A
$I_{CM}$	Collector current-peak		30	A
$P_T$	Total power dissipation	$T_C=25$	100	W
		$T_a=25$	3.0	
$T_j$	Junction temperature		150	
$T_{stg}$	Storage temperature		-55~150	

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## CHARACTERISTICS

T<sub>j</sub>=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =30mA ; I <sub>B</sub> =0	100			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =15A ; I <sub>B</sub> =30mA			1.5	V
V <sub>BEsat</sub>	Base-emitter saturation voltage	I <sub>C</sub> =15A ; I <sub>B</sub> =30mA			2.2	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =100V; I <sub>E</sub> =0			10	μA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =5V; I <sub>C</sub> =0			5	mA
h <sub>FE</sub>	DC current gain	I <sub>C</sub> =15A ; V <sub>CE</sub> =2V	1000		30000	

## Switching times

t <sub>on</sub>	Turn-on time	I <sub>C</sub> =15A; I <sub>B1</sub> =-I <sub>B2</sub> =30mA V <sub>CC</sub> 60V; R <sub>L</sub> =4Ω		1.0		μs
t <sub>stg</sub>	Storage time			5.0		μs
t <sub>f</sub>	Fall time			2.0		μs

◆ h<sub>FE</sub> Classifications

M	L	K	J
1000-3000	2000-5000	4000-10000	8000-30000

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PACKAGE OUTLINE

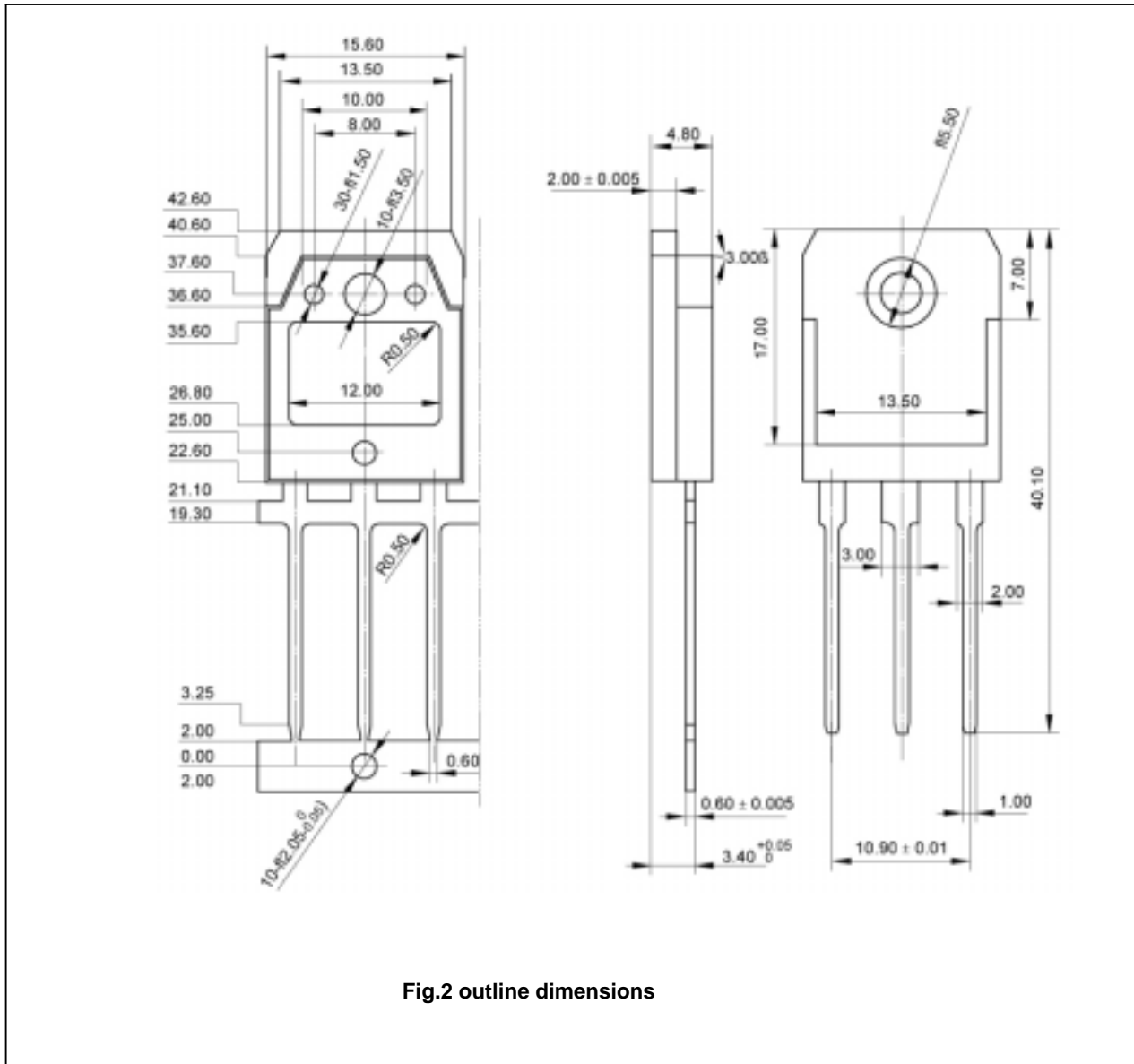


Fig.2 outline dimensions